











LM158, LM158A, LM258, LM258A LM358, LM358A, LM358B, LM2904, LM2904B, LM2904V

SLOS068V - JUNE 1976-REVISED SEPTEMBER 2018

Industry-Standard Dual Operational Amplifiers

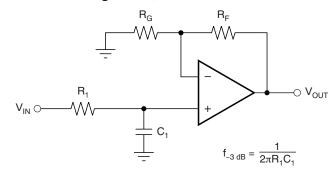
1 Features

- Wide Supply Range of 3 V to 36 V (B Version)
- Supply-Current of 300 μA (B Version, Typical)
- Unity-Gain Bandwidth of 1.2 MHz (B Version)
- Common-Mode Input Voltage Range Includes Ground, Enabling Direct Sensing Near Ground
- Low Input Offset Voltage of 3 mV at 25°C (A and B Versions, Maximum)
- · Internal RF and EMI Filter (B Version)
- On Products Compliant to MIL-PRF-38535, All Parameters Are Tested Unless Otherwise Noted. On All Other Products, Production Processing Does Not Necessarily Include Testing of All Parameters.

2 Applications

- Merchant Network and Server Power Supply Units
- Multi-Function Printers
- Power Supplies and Mobile Chargers
- Motor Control: AC Induction, Brushed DC, Brushless DC, High-Voltage, Low-Voltage, Permanent Magnet, and Stepper Motor
- Desktop PC and Motherboard
- Indoor and Outdoor Air Conditioners
- · Washers, Dryers, and Refrigerators
- AC Inverters, String Inverters, Central Inverters, and Voltage Frequency Drives
- Uninterruptible Power Supplies
- Programmable Logic Controllers
- · Electronic Point-of-Sale Systems

Single-Pole, Low-Pass Filter



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_1C_1}\right)$$

3 Description

The LM358B and LM2904B devices are the next-generation versions of the industry-standard LM358 and LM2904 devices, which include two high-voltage (36-V) operational amplifiers (op amps). These devices provide outstanding value for cost-sensitive applications, with features including low offset (300 μ V, typical), common-mode input range to ground, and high differential input voltage capability.

The LM358B and LM2904B devices simplify circuit design with enhanced features such as unity-gain stability, lower offset voltage of 3 mV (maximum at room temperature), and lower quiescent current of 300 μ A (typical). High ESD (2 kV, HBM) and integrated EMI and RF filters enable the LM358B and LM2904B devices to be used in the most rugged, environmentally challenging applications.

The LM358B and LM2904B devices are available in micro-size packages, such as TSOT-8 and WSON, as well as industry standard packages, including SOIC, TSSOP, and VSSOP.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)					
LM358B ⁽²⁾ , LM2904B ⁽²⁾ , LM358, LM358A,LM2904, LM2904V, LM258, LM258A	SOIC (8)	4.90 mm × 3.90 mm					
LM358, LM358A, LM2904, LM2490V	TSSOP (8)	3.00 mm × 4.40 mm					
LM358, LM358A LM2904, LM2904V, LM258, LM258A	VSSOP (8)	3.00 mm × 3.00 mm					
LM358, LM2904	SO (8)	5.20 mm × 5.30 mm					
LM358, LM2904, LM358A, LM258, LM258A	PDIP (8)	9.81 mm × 6.35 mm					
LM158, LM158A	CDIP (8)	9.60 mm × 6.67 mm					
LM158, LM158A	LCCC (20)	8.89 mm × 8.89 mm					

- (1) For all available packages, see the orderable addendum at the end of the data sheet.
- (2) Package is for preview only



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cr	nanges from Revision U (January 2017) to Revision V	Page
•	Changed the data sheet title	1
•	Changed first four items in the Features section	1
•	Changed the first item in the Applications section and added four new items	1
•	Changed voltage values in the first paragraph of the Description section	1
•	Changed text in the second paragraph of the Description section	1
•	Added devices LM358B and LM2904B to data sheet	1
•	Changed the first three rows of the <i>Device Information</i> table and added a a cross-referenced note for PREVIEW-status devices	1
•	Added Device Comparison table	4
•	Added a table note to the Pin Functions table	5
•	Changed "free-air temperature" to "ambient temperature" in the Absolute Maximum Ratings condition statement	6
•	Changed all entries in the Absolute Maximum Ratings table except T _J and T _{stg}	6
•	Deleted lead temperature and case temperature from Absolute Maximum Ratings	
•	Changed device listings and their voltage values in the ESD Ratings table	6
•	Changed "free-air temperature" to "ambient temperature" in the Recommended Operating Conditions condition statement	7
•	Changed table entries for all parameters in the Recommended Operating Conditions table	7
•	Added rows to the Thermal Information table, and a table note regarding device-package combinations	7
•	Added two Electrical Characteristics tables with five additional devices, and redistributed the seven original devices differently among the tables	
•	Deleted the Operating Conditions table	
•	Added a condition statement to the Typical Characteristics section	14
•	Changed specific voltages to a Recommended Operating Conditions reference	17





Revision History (continued)

		4.0
•	Changed unity-gain bandwidth from 0.7 MHz for all devices to 1.2 MHz for B-version devices	
•	Changed slew rate from 3 V/µs for all devices to 0.5 V/µs for B-version devices	18
•	Changed the Input Common Mode Range section in multiple places throughout	18
•	Changed V _{CC} to V _S in the Application Information section	19
•	Subscripted the suffixes fro R _I and R _F	19
•	Changed Operational Amplifier Board Layout for Noninverting Configuration with an image that includes a dual op a	mp 21
<u>•</u>	Added Preview designation to the LM358B and LM2904B devices in Table 1	22
Cł	nanges from Revision T (April 2015) to Revision U	Page
•	Changed data sheet title	1
<u>•</u>	Added Receiving Notification of Documentation Updates section and Community Resources section	22
Cł	nanges from Revision S (January 2014) to Revision T	Page
•	Added Applications section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	1
Cł	nanges from Revision R (July 2010) to Revision S	Page
•	Converted this data sheet from the QS format to DocZone using the PDF on the web	1
•	Deleted Ordering Information table	1
•	Updated Features to include Military Disclaimer	1
•	Added Typical Characteristics section	14
•	Added ESD warning	23



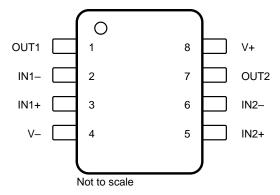
5 Device Comparison Table

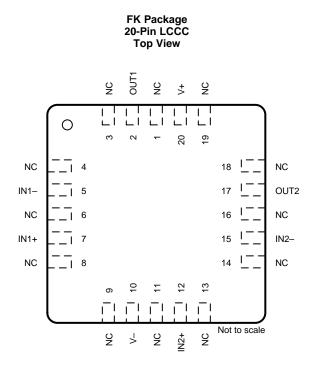
PART NUMBER	SUPPLY VOLTAGE	TEMPERATURE RANGE	V _{OS} (MAXIMUM AT 25°C)	I _Q / CH (TYPICAL AT 25°C)	INTEGRATED EMI FILTER	PACKAGE
LM358B	3 V–36 V	-40°C to 85°C	3 mV	300 μΑ	Yes	D, PW
LM2904B	3 V–36 V	-40°C to 125°C	3 mV	300 μΑ	Yes	D, PW
LM358	3 V–32 V	0°C to 70°C	7 mV	350 μΑ	No	D, PW, DGK, P, PS
LM2904	3 V–26 V	-40°C to 125°C	7 mV	350 µA	No	D, PW, DGK, P, PS
LM358A	3 V–32 V	0°C to 70°C	3 mV	350 µA	No	D, PW, DGK, P
LM2904V	3 V–32 V	-40°C to 125°C	3 mV	350 μΑ	No	D, PW
LM158	3 V–32 V	–55°C to 125°C	5 mV	350 µA	No	JG, FK
LM158A	3 V–32 V	–55°C to 125°C	3 mV	350 μΑ	No	JG, FK
LM258	3 V–32 V	-25°C to 85°C	5 mV	350 μΑ	No	D, DGK, P
LM258A	3 V-32 V	-25°C to 85°C	3 mV	350 µA	No	D, DGK, P



6 Pin Configuration and Functions

D, DGK, P, PS, PW, and JG Packages 8-Pin SOIC, VSSOP, PDIP, SO, TSSOP, and CDIP Top View





NC - No internal connection

Pin Functions

	ı	PIN	I/O	DESCRIPTION
NAME	LCCC ⁽¹⁾	SOIC, SSOP, CDIP, PDIP, SO, TSSOP, CFP ⁽¹⁾		
IN1-	5	2	I	Negative input
IN1+	7	3	I	Positive input
IN2-	15	6	1	Negative input
IN2+	12	5	1	Positive input
OUT1	2	1	0	Output
OUT2	17	7	0	Output
V–	10	4	_	Negative (lowest) supply or ground (for single-supply operation)
NC	1, 3, 4, 6, 8, 9, 11, 13, 14, 16, 18, 19	_	_	No internal connection
V+	20	8	_	Positive (highest) supply

⁽¹⁾ For a listing of which devices are available in what packages, see Device Comparison Table.



7 Specifications

7.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
		LM358B, LM358BA, LM2904B, LM2904BA	-0.3	±20 or 40	
Supply voltage, $V_S = ([V+] - [V-])$		LM158, LM258, LM358, LM158A, LM258A, LM358A, LM2904V	-0.3	±16 or 32	V
		LM2904	-0.3	±20 or 40 ±16 or 32 ±13 or 26 32 26 40 32 26 Unlimited 125 85 70 125	
Differential input voltage, V _{ID} ⁽²⁾	LM358B, LM358BA, LM2904B, LM2904BA,LM158, LM258, LM358, LM158A, LM258A, LM358A, LM2904V	-32	32	V	
		LM2904	-26	26	
		LM358B, LM358BA, LM2904B, LM2904BA	-0.3	40	
Input voltage, V _I	Either input	LM158, LM258, LM358, LM158A, LM258A, LM358A, LM2904V	-0.3	32	V
		LM2904	-0.3	26	
Duration of output short circuit (one amplif $V_S \le 15 \ V^{(3)}$	ier) to ground at (o	r below) T _A = 25°C,		Unlimited	s
		LM158, LM158A	-55	125	
		LM258, LM258A	-25	85	
Operating ambient temperature, T _A		LM358B, LM358BA	-40	85	°C
operating ambient temperature, 14		LM358, LM358A	0	70	Ü
		LM2904B, LM2904BA, LM2904, LM2904V	-40	125	
Operating virtual-junction temperature, T _J				150	°C
Storage temperature, T _{stg}	·		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT					
LM358B, LM358BA, LM2904B, AND LM2904BA									
\/ Flastrastatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		±2000	V					
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)		V					
LM158,	LM158, LM258, LM358, LM158, LM258A, LM358A, LM2904, AND LM2904V								
V	Floatroototic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)		V					
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	\ \ \					

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ Differential voltages are at IN+, with respect to IN-

⁽³⁾ Short circuits from outputs to V_S can cause excessive heating and eventual destruction.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	MAX	UNIT
	Supply voltage, V _S = ([V+] – [V–])	LM358B, LM358BA, LM2904B, LM2904BA	3	36	
Vs		LM158, LM258, LM358, LM158A, LM258A, LM358A, LM2904V	3	30	V
		LM2904	3	26	
V_{CM}	Common-mode voltage		V-	V _S – 2	V
		LM358B, LM358BA	-40	85	
		LM2904B, LM2904BA, LM2904, LM2904V	-40	125	_
T _A	Operating ambient temperature	LM358, LM358A	0	70	°C
		LM258, LM258A	-20	85	
		LM158, LM158A	-55	125	

7.4 Thermal Information

	ionna inionnation								1
		LM258, LM258A, LM358, LM358A, LM358B, LM358BA, LM2904, LM2904B, LM2904BA, LM2904V ⁽²⁾				LM158, LM158A			
	THERMAL METRIC ⁽¹⁾		DGK (VSSOP)	P (PDIP)	PS (SO)	PW (TSSOP)	FK (LCCC)	JG (CDIP)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	8 PINS	20 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	124.7	181.4	80.9	116.9	171.7	_	_	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	66.9	69.4	70.4	62.5	68.8	5.61	14.5	°C/W
R _{0JB}	Junction-to-board thermal resistance	67.9	102.9	57.4	68.6	99.2	_	_	°C/W
ΨЈТ	Junction-to-top characterization parameter	19.2	11.8	40	21.9	11.5	_	_	°C/W
ΨЈВ	Junction-to-board characterization parameter	67.2	101.2	56.9	67.6	97.9	_	_	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	_	_	_	_	_	12.1	_	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.

⁽²⁾ For a listing of which devices are available in what packages, see Device Comparison Table



7.5 Electrical Characteristics: LM358B and LM358BA

For $V_S = (V+) - (V-) = 5 \text{ V}$ to 36 V (±2.25 V to ±18 V), $T_A = 25 \,^{\circ}\text{C}$, $R_L = 10 \,\text{k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$ (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
OFFSET V	OLTAGE						
					1	3	
		LM358B	T _A = -40°C to 85°C			4	
Vos	Input offset voltage		A		0.5	1.8	mV
		LM358BA	T _A = -40°C to 85°C			2.5	
dV _{OS} /dT	Input offset voltage drift		$T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}$		±3.5	2.0	μV/°C
uv _{0S} /u1	Power-supply rejection		14 - 40 0 10 00 0		10.0		μν/ Ο
PSRR	ratio				±1	15	μV/V
	$(\Delta V_{IO}/\Delta V_{S})$						
	Channel separation, dc	At dc			120		dB
INPUT VOL	TAGE RANGE						
V _{CM}	Common-mode input	V _S = 3 V to 36 V		(V-)		(V+) - 1.5	V
V CM	voltage range	V _S = 3 V to 30 V	$T_A = -40$ °C to 85°C	(V-)		(V+) - 2	v
CMRR	Common-mode rejection	$(V-) < V_{CM} < (V+) - 1.5 V$		80	103		dB
CIVIRR	ratio	(V-) < V _{CM} < (V+) - 2 V	$T_A = -40$ °C to 85°C	70	96		uв
INPUT BIAS	S CURRENT					,	
					10	35	
I _B	Input bias current		$T_A = -40$ °C to 85°C			50	nA
					0.5	4	
Ios	Input offset current		T ₄ = −40°C to 85°C			5	nA
NOISE							
En	Input voltage noise	f = 0.1 to 10 Hz			8		μV _{PP}
e _n	Input voltage noise density	f = 1 kHz			40		nV/√Hz
INPUT IMP		<i>y</i> =					
Z _{ID}	Differential				10 0.1		MΩ pF
Z _{IC}	Common-mode				4 1.5		GΩ pF
OPEN-LOO					4 1.5		Gtz pr
OF LIV-LOO	OF GAIN			70	140		
A _{OL}	Open-loop voltage gain	$V_S = 15 \text{ V}, V_O = 1 \text{ V to } 11 \text{ V}, R_L \ge 2 \text{ k}\Omega$	T 40%C to 05%C		140		V/mV
	0V DE0D0110E		$T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}$	35			
	CY RESPONSE						
GBW	Gain-bandwidth product				1.2		MHz
SR	Slew rate	G = +1			0.5		V/µs
φ _m	Phase margin	$G = +1$, $R_L = 10$ kΩ, $C_L = 20$ pF			56		0
t _S	Settling time	To 0.1%, $V_S = 5 \text{ V}$, 2-V step , $G = +1$, C	_L = 100 pF		4		μs
t _{OR}	Overload recovery time	V _{IN} × gain > V _S			30		μs
THD + N	Total harmonic distortion + noise	$G = +1, f = 1 \text{ kHz}, V_O = 3.53 V_{RMS}, RL$	= 100 kΩ		0.001%		
OUTPUT	110100						
0011 01			I _{OUT} = 50 μA		1.35	1.5	
		Positive Rail (\/+)					
V	Voltage output swing from	Positive Rail (V+)	I _{OUT} = 1 mA		1.4	1.6	V
Vo	rail		I _{OUT} = 5 mA		1.5		V
		Negative Rail (V-)	I _{OUT} = 50 μA		0.1	0.15	
	0	V 99.V	I _{OUT} = 1 mA		0.75	1	
I _{SC}	Short-circuit current	V _S = 20 V			±40	60	mA -
C _{LOAD}	Capacitive load drive				100		pF
R_{O}	Open-loop output resistance	$f = 1 \text{ MHz}, I_O = 0 \text{ A}$			300		Ω
POWER SU		1					
. 5	-	V _S = 5 V; V _O = 2.5 V; I _O = 0 A			300	460	
IQ	Quiescent current per amplifier		T _A = - 40°C to 85°C		300	800	μΑ
		$V_S = 36 \text{ V}; V_O = 2.5 \text{ V}; I_O = 0 \text{ A}$	1A = - 40°C 10 85°C			800	

⁽¹⁾ All typical values are $T_A = 25$ °C.



7.6 Electrical Characteristics: LM2904B and LM2904BA

For $V_S = (V+) - (V-) = 5 \text{ V}$ to 36 V (±2.25 V to ±18 V), $T_A = 25 \,^{\circ}\text{C}$, $R_L = 10 \,\text{k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$ (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	MIN	TYP ⁽¹⁾	MAX	UNIT
OFFSET	VOLTAGE						
		LM0004D			1	3	
\ <i>'</i>	lanut offeet veltere	LM2904B	$T_A = -40$ °C to 125°C			4	\/
Vos	Input offset voltage	LM2904BA			0.5	1.8	mV
		LM2904BA	T _A = -40°C to 125°C			2.5	
dV _{OS} /dT	Input offset voltage drift		T _A = -40°C to 125°C		±3.5		μV/°C
PSRR	Power-supply rejection ratio $(\Delta V_{IO}/\Delta V_S)$,		±1	15	μV/V
	Channel separation, dc	At dc			120		dB
INPUT VO	OLTAGE RANGE						
V	Common-mode input voltage	V 2 V 4= 26 V		(V-)		(V+) - 1.5	V
V _{CM}	range	V _S = 3 V to 36 V	T _A = -40°C to 125°C	(V-)		(V+) - 2	V
CMDD	Common mode rejection retio	(V-) < V _{CM} < (V+) - 1.5 V		80	103		٩D
CMRR	Common-mode rejection ratio	(V-) < V _{CM} < (V+) - 2 V	T _A = -40°C to 125°C	70	96		dB
INPUT BI	AS CURRENT						
	Input bias current				10	35	- A
l _B	input bias current		T _A = -40°C to 125°C			50	nA
	Innut offeet coment				0.5	4	- A
los	Input offset current		T _A = -40°C to 125°C			5	nA
NOISE							
E _n	Input voltage noise	f = 0.1 to 10 Hz			8		μV_{PP}
e _n	Input voltage noise density	f = 1 kHz			40		nV/√ Hz
INPUT IM	PEDANCE						
Z _{ID}	Differential				10 0.1		MΩ pF
Z _{IC}	Common-mode				4 1.5		GΩ pF
OPEN-LO	OOP GAIN		·				
^	Ones lees volters sein	V 45 V V 4 V to 44 V D > 2 to		70	140		V/mV
A _{OL}	Open-loop voltage gain	$V_S = 15 \text{ V}; V_O = 1 \text{ V to } 11 \text{ V}; R_L \ge 2 \text{ k}\Omega$	$T_A = -40$ °C to 125°C	35			V/IIIV
FREQUE	NCY RESPONSE						
GBW	Gain-bandwidth product				1.2		MHz
SR	Slew rate	G = +1			0.5		V/µs
ϕ_{m}	Phase margin	$G = +1, R_L = 10 \text{ k}\Omega, C_L = 20 \text{ pF}$			56		0
t _S	Settling time	To 0.1%, V_S = 5 V, 2-V step , G = +1, C_L =	100 pF		4		μs
t _{OR}	Overload recovery time	V _{IN} × gain > V _S			30		μs
THD + N	Total harmonic distortion + noise	G = +1, f = 1 kHz, V_0 = 3.53 V_{RMS} , RL = 10	0 kΩ		0.001%		
OUTPUT						<u></u>	
			I _{OUT} = 50 μA		1.35	1.5	
		Positive rail (V+)	I _{OUT} = 1 mA		1.4	1.6	
V_{O}	Voltage output swing from rail		I _{OUT} = 5mA		1.5	1.75	V
		Negative rail (V–)	I _{OUT} = 50 μA		0.1	0.15	
		ivegative fall (v-)	I _{OUT} = 1 mA		0.75	1	
I _{SC}	Short-circuit current	V _S = 20 V			±40	60	mA
C _{LOAD}	Capacitive load drive				100		pF
Ro	Open-loop output resistance	f = 1 MHz, I _O = 0 A			300		Ω
POWER S	SUPPLY						
	0	V _S = 5 V; V _O = 2.5 V; I _O = 0 A			300	460	
lα	Quiescent current per amplifier	V _S = 36 V; V _O = 2.5 V; I _O = 0 A	T _Δ = -40°C to 125°C			800	μA

⁽¹⁾ All typical values are $T_A = 25$ °C.



7.7 Electrical Characteristics: LM358, LM358A

For $V_S = (V+) - (V-) = 5 \text{ V}$, $T_A = 25 ^{\circ}\text{C}$, (unless otherwise noted)

	PARAMETER		TEST COND	DITIONS(1)		MIN	TYP ⁽²⁾	MAX	UNIT
OFFSET	VOLTAGE								
							3	7	
		V = 5 V to 30 V: V = 0) \/· \/ _ 1 1	LM358	T _A = 0°C to 70°C			9	
/os	Input offset voltage	$V_S = 5 \text{ V to } 30 \text{ V}; V_{CM} = 0$	7 v, v ₀ = 1.4	LM358A	A		2	3	mV
					T _A = 0°C to 70°C			5	
				LM358	T _A = 0°C to 70°C		7		
dV_{OS}/d_{T}	Input offset voltage drift			LM358A	T _A = 0°C to 70°C		7	20	μV/°C
	Input offset voltage vs power			LIVIOSOA	1 _A = 0 0 to 70 0			20	
PSRR	supply $(\Delta V_{IO}/\Delta V_{S})$	V _S = 5 V to 30 V				65	100		dB
/ ₀₁ / V ₀₂	Channel separation	f = 1 kHz to 20 kHz					120		dB
	OLTAGE RANGE								
		V _S = 5 V to 30 V		LM358					
		V _S = 30 V		LM358A		(V–)		(V+) - 1.5	
/ _{CM}	Common-mode voltage range	V _S = 5 V to 30 V		LM358					V
		V _S = 30 V		LM358A	$T_A = 0$ °C to 70°C	(V-)		(V+) - 2	
CMRR	Common mode rejection ratio) V	LIVISSOA		65	80		dB
	Common-mode rejection ratio	$V_S = 5 \text{ V to } 30 \text{ V; } V_{CM} = 0$) V			65	80		иь
NPULBI	AS CURRENT							050	
				LM358	T 000 : 7000		-20	-250	
В	Input bias current	V _O = 1.4 V			$T_A = 0$ °C to 70°C			-500	nA
				LM358A			-15	-100	
					$T_A = 0$ °C to 70°C			-200	
				LM358			2	50	
	Input offset current	V _O = 1.4 V		LIVIOOO	$T_A = 0$ °C to 70 °C			150	nA
os	input onset current	V ₀ = 1.4 V		LM358A			2	30	шА
				LIVISSOA	$T_A = 0$ °C to 70 °C			75	
							10		1.00
dl _{os} /d _T	Input offset current drift			LM358A	T _A = 0°C to 70°C			300	pA/°C
NOISE		II.		1				I	
e _n	Input voltage noise density	f = 1 kHz					40		nV/√Hz
	OOP GAIN								
						25	100		
A _{OL}	Open-loop voltage gain	$V_S = 15 \text{ V}; V_O = 1 \text{ V to } 11$	1 V; $R_L \ge 2 k\Omega$		T _A = 0°C to 70°C	15			V/mV
ERECUE	NCY RESPONSE				1 _A = 0 0 to 10 0				
GBW	Gain bandwidth product						0.7		MHz
SR	Slew rate	G = +1					0.3		V/µs
	Siew late	G = +1					0.3		ν/μ5
DUTPUT			14 00 14 B	010	T 000 / 7000				
			V _S = 30 V; R _I		T _A = 0°C to 70°C			4	
/ ₀	Voltage output swing from rail	Positive rail	$V_S = 30 \text{ V; R}_1$				2	3	V
			$V_S = 5 \text{ V}; R_L$					1.5	
		Negative rail	$V_S = 5 \text{ V}; R_L$	≤ 10 kΩ	$T_A = 0$ °C to 70°C		5	20	mV
		V 45.V.V 0.V.V				-20	-30		
		V _S = 15 V; V _O = 0 V; V _{ID} = 1 V	Source	LM358A				-60	
					$T_A = 0$ °C to 70°C	-10			mA
0	Output current					10	20		
		$V_S = 15 \text{ V}; V_O = 15 \text{ V}; V_{ID} = -1 \text{ V}$	Sink		T _A = 0°C to 70°C	5			
		- u		LM358		12			
		V _{ID} = -1 V; V _O = 200 mV	1				30		μΑ
sc	Short-circuit current	V _S = 10 V; V _O = V _S / 2					±40	±60	mA
POWER S									
		V _O = 2.5 V; I _O = 0 A					350	600	
Q	Quiescent current per amplifier	V _S = 30 V; V _O = 15 V; I _O	- 0 Δ		T _A = 0°C to 70°C		500	1000	μΑ
	inferiores	v _S = 30 v, v _O = 15 V; I _O	- U A				ວບປ	1000	

⁽¹⁾ All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified. Maximum V_S for testing purposes is 30 V for LM358 and LM358A.

⁽²⁾ All typical values are $T_A = 25$ °C.



7.8 Electrical Characteristics: LM2904, LM2904V

For $V_S = (V+) - (V-) = 5 V$, $T_A = 25 °C$, (unless otherwise noted)

	PARAMETER		TES	T COND	TIONS ⁽¹⁾		MIN	TYP (2)	MAX	UNIT
OFFSET	VOLTAGE	'								
					Non-A suffix			3	7	
		// = 5 // to maxii	mum: \/ = 0 \/: \/	_11	devices	T _A = -40°C to 125°C			10	
Vos	Input offset voltage	V _S = 5 V to maxii	mum; $V_{CM} = 0 \text{ V}$; $V_{CM} = 0 \text{ V}$	0 = 1.4	A auttiv	A		1	2	mV
					A-suffix devices	T _A = -40°C to 125°C			4	
dV _{OS} /d _T	Input offset voltage drift					$T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$		7		μV/°C
	Input offset voltage vs power					1 _A = 10 0 to 120 0				
PSRR	supply $(\Delta V_{IO}/\Delta V_S)$	V _S = 5 V to 30 V					65	100		dB
V _{O1} / V _{O2}	Channel separation	f = 1 kHz to 20 k	Hz					120		dB
INPUT V	OLTAGE RANGE									
.,	0 1 1						(V-)		(V+) - 1.5	.,
V _{CM}	Common-mode voltage range	V _S = 5 V to maxi	mum			T _A = -40°C to 125°C	(V-)		(V+) - 2	V
CMRR	Common-mode rejection ratio	V _S = 5 V to maxi	mum; V _{CM} = 0 V			II.	65	80		dB
INPUT BI	AS CURRENT						I			l .
								-20	-250	
I _B	Input bias current	V _O = 1.4 V				T _A = -40°C to 125°C			-500	nA
					Non-V suffix	A		2	50	
					device	T _A = -40°C to 125°C			300	
los	Input offset current	V _O = 1.4 V			V #:	7A 10 0 to 120 0		2	50	nA
					V-suffix device	T _A = -40°C to 125°C			150	
dl _{OS} /d _T	Input offset current drift					$T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$		10	130	pA/°C
NOISE	input onset current unit					1 _A = -40 0 to 125 0		10		prv O
	Input voltage poins density	f = 1 kHz						40		nV/√ Hz
e _n	Input voltage noise density	I = I KHZ						40		IIV/VHZ
OPEN-LC	OOP GAIN							400		
A _{OL}	Open-loop voltage gain	V _S = 15 V; V _O =	1 V to 11 V; R _L ≥ 2	$k\Omega$		T 4000 4 40500	25	100		V/mV
						$T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	15			
	NCY RESPONSE									
GBW	Gain bandwidth product							0.7		MHz
SR	Slew rate	G = +1						0.3		V/µs
OUTPUT		T	T				1			1
			R _L ≥ 10 kΩ	1		T	V _S – 1.5			
				$V_S = ma$ 2 k Ω	aximum; R _L =		22			
			Non-V suffix device		aximum; R _L ≥	-				
		Positive rail		V _S = 1116 10 kΩ	axiiiiuiii, K∟ ≥		23	24		V
Vo	Voltage output swing from rail				aximum; R _L =	$T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	26			
			V-suffix device	2 kΩ			20			
				$V_S = ma$ $10 \text{ k}\Omega$	aximum; R _L ≥		27	28		
		Negative rail			/· B < 10 k0	T _A = -40°C to 125°C		5	20	mV
		Negative rail		V _S = 3	V, INL = 10 K32	1 _A = -40 C to 125 C	-20	-30	20	IIIV
		V _S = 15 V; V _O = 0	$V; V_{ID} = 1 V$	Source		T _A = -40°C to 125°C		-30		
						T _A = -40°C to 125°C	-10			mA
lo	Output current	V _S = 15 V; V _O =	15 V; V _{ID} = −1 V	Sink		T 4000 4 40500	10	20		
				$T_A = -40$ °C to 125°C			5			
		V _{ID} = -1 V; V _O = 2	200 mV	-	suffix device			30		μA
	- · · · · ·			V-suffix	device		12	40		_
I _{sc}	Short-circuit current	V _S = 10 V; V _O = 1	V _S / 2					±40	±60	mA
POWER	SUPPLY									
lα	Quiescent current per amplifier	$V_0 = 2.5 \text{ V}; I_0 = 0$				T _A = -40°C to 125°C		350	600	μA
u.		V _S = maximum; \	$I_0 = \text{maximum} / 2;$; I _O = 0 A				500	1000	ļ ,

⁽¹⁾ All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified. Maximum V_S for testing purposes is 26 V for LM2904 and 32 V for LM2904V.

⁽²⁾ All typical values are $T_A = 25$ °C.



7.9 Electrical Characteristics: LM158, LM158A

For $V_S = (V+) - (V-) = 5 \text{ V}$, $T_A = 25 ^{\circ}\text{C}$, (unless otherwise noted)

	$= (V+) - (V-) = 5 V, I_A = $		ST COND			MIN	TYP ⁽²⁾	MAX	UNIT
OFFSET	VOLTAGE								
							3	5	
				LM158	T _A = -55°C to 125°C			7	
Vos	Input offset voltage	$V_S = 5 \text{ V to } 30 \text{ V; } V_{CM} = 0 \text{ V; } V_{C}$) = 1.4 V					2	mV
				LM158A	T _A = -55°C to 125°C			4	
				LM158	T _A = -55°C to 125°C		7		
dV _{OS} /d _T	Input offset voltage drift			LM158A	T _A = -55°C to 125°C		7	15 ⁽³⁾	μV/°C
PSRR	Input offset voltage vs power supply	V _S = 5 V to 30 V				65	100		dB
	$(\Delta V_{IO}/\Delta V_{S})$								
V _{O1} / V _{O2}	· · · · · · · · · · · · · · · · · · ·	f = 1 kHz to 20 kHz					120		dB
INPUT V	OLTAGE RANGE								
		V _S = 5 V to 30 V		LM158		(V-)		(V+) - 1.5	
V_{CM}	Common-mode voltage range	V _S = 30 V		LM158A					V
		V _S = 5 V to 30 V		LM158	T _A = -55°C to 125°C	(V-)		(V+) - 2	
		V _S = 30 V		LM158A					
CMRR	Common-mode rejection ratio	$V_S = 5 \text{ V to } 30 \text{ V}; V_{CM} = 0 \text{ V}$				70	80		dB
INPUT B	IAS CURRENT								
				LM158			-20	-150	
l _B	Input bias current	V _O = 1.4 V			T _A = -55°C to 125°C			-300	nA
				LM158A			-15	-50	
					T _A = -55°C to 125°C			-100	
				LM158			2	30	
los	Input offset current	V _O = 1.4 V			T _A = -55°C to 125°C			100	nA
				LM158A			2	10	
					T _A = -55°C to 125°C			30	
dl _{os} /d _T	Input offset current drift						10		pA/°C
				LM158A	$T_A = -55^{\circ}C \text{ to } 125^{\circ}C$			200	
NOISE	1 4 6 1 1 9								\//
e _n	Input voltage noise density	f = 1 kHz					40		nV/√Hz
OPEN-L	OOP GAIN								
A _{OL}	Open-loop voltage gain	$V_S = 15 \text{ V}; V_O = 1 \text{ V to } 11 \text{ V}; R_L$	≥ 2 kΩ		T 5500 4 40500	50	100		V/mV
FREGUE	NOV DECRONOE				$T_A = -55^{\circ}C \text{ to } 125^{\circ}C$	25			
	Coin handwidth product						0.7		NAL I-
GBW SR	Gain bandwidth product	C .11					0.7		MHz
SK	Slew rate	G = +1							V/µs
			V _S = 30 \	$/; R_L = 2 k\Omega$	T _A = -55°C to 125°C			4	
Vo	Voltage output swing from rail	Positive rail	V _S = 30 \	/; R _L ≥ 10 kΩ			2	3	V
•0	renage carpar enting nem ran		V _S = 5 V;	$R_L \ge 2 \ k\Omega$				1.5	
		Negative rail	V _S = 5 V;	$R_L \le 10 \text{ k}\Omega$	T _A = -55°C to 125°C		5	20	mV
						-20	-30		
		V _S = 15 V; V _O = 0 V; V _{ID} = 1 V Source LM158		LM158A				-60	
l _o	Output current				T _A = -55°C to 125°C	-10			mA
J		$V_S = 15 \text{ V}; V_O = 15 \text{ V}; V_{ID} = -1$	Sink			10	20		
		V			T _A = -55°C to 125°C	5			
		$V_{ID} = -1 \text{ V}; V_{O} = 200 \text{ mV}$				12	30		μA
I _{SC}	Short-circuit current	$V_S = 10 \text{ V}; V_O = V_S / 2$					±40	±60	mA
POWER	SUPPLY	1			1				
lα	Quiescent current per amplifier	V _O = 2.5 V; I _O = 0 A			T _A = -55°C to 125°C		350	600	μA
۷.	and the second s	$V_S = 30 \text{ V}; V_O = 15 \text{ V}; I_O = 0 \text{ A}$					500	1000	1000

All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified. Maximum V_S for testing purposes is 30 V for LM158 and LM158A.

⁽²⁾ All typical values are T_A = 25°C.

⁽³⁾ On products compliant to MIL-PRF-38535, this parameter is not production tested.



7.10 Electrical Characteristics: LM258, LM258A

For $V_S = (V+) - (V-) = 5 \text{ V}$, $T_A = 25 ^{\circ}\text{C}$, (unless otherwise noted)

	$= (V+) - (V-) = 5 V, I_A = $		ST COND			MIN	TYP ⁽²⁾	MAX	UNIT
OFFSET	VOLTAGE								
							3	5	
				LM258	T _A = -25°C to 85°C			7	
Vos	Input offset voltage	$V_S = 5 \text{ V to } 30 \text{ V; } V_{CM} = 0 \text{ V; } V_C$	o = 1.4 V		1 _A = -23 0 to 63 0		2	3	mV
				LM258A	T _A = -25°C to 85°C			4	
				LM258	T _A = -25°C to 85°C		7	4	
dV _{OS} /d _T	Input offset voltage drift			LM258A	$T_A = -25^{\circ}\text{C to } 85^{\circ}\text{C}$		7	15	μV/°C
	Input offset voltage vs power supply			LIVIZOOA	1 _A = -23 0 to 63 0			13	
PSRR	$(\Delta V_{IO}/\Delta V_S)$	V _S = 5 V to 30 V				65	100		dB
V ₀₁ / V ₀₂	Channel separation	f = 1 kHz to 20 kHz					120		dB
INPUT V	OLTAGE RANGE								
		V _S = 5 V to 30 V		LM258		()/)		()(1) 15	
V	Common mode valters rooms	V _S = 30 V		LM258A		(V–)		(V+) – 1.5	V
V _{CM}	Common-mode voltage range	V _S = 5 V to 30 V		LM258	T 2500 to 0500	()()		()(1) 2	V
		V _S = 30 V		LM258A	$T_A = -25^{\circ}\text{C to } 85^{\circ}\text{C}$	(V–)		(V+) – 2	
CMRR	Common-mode rejection ratio	V _S = 5 V to 30 V; V _{CM} = 0 V				70	80		dB
INPUT B	SIAS CURRENT				•				
				LMOEG			-20	-150	
	band bing assessed	N 44N		LM258	$T_A = -25$ °C to 85°C			-300	4
I _B	Input bias current	V _O = 1.4 V		LMOTOA			-15	-80	nA
				LM258A	$T_A = -25$ °C to 85°C			-100	
				LMOSO			2	30	
	land offer a comment	V 44V		LM258	$T_A = -25$ °C to 85°C			100	4
los	Input offset current	V _O = 1.4 V		1110501			2	15	nA
				LM258A	$T_A = -25$ °C to 85°C			30	
							10		1/00
dl _{OS} /d _T	Input offset current drift			LM258A	$T_A = -25$ °C to 85°C			200	pA/°C
NOISE									
e _n	Input voltage noise density	f = 1 kHz					40		nV/√ Hz
OPEN-L	OOP GAIN				<u> </u>				
	0 1 1 1	45444 444 5				50	100		
A _{OL}	Open-loop voltage gain	$V_S = 15 \text{ V}; V_O = 1 \text{ V to } 11 \text{ V}; R_I$	_ ≥ 2 KΩ		$T_A = -25$ °C to 85°C	25			V/mV
FREQUE	NCY RESPONSE	•			<u> </u>			•	
GBW	Gain bandwidth product						0.7		MHz
SR	Slew rate	G = +1					0.3		V/µs
OUTPUT	г								
			V _S = 30 \	V ; $R_L = 2 k\Omega$	$T_A = -25^{\circ}\text{C to } 85^{\circ}\text{C}$			4	
V	Voltage autout autie a frame sail	Positive rail	V _S = 30 \	/; R _L ≥ 10 kΩ			2	3	V
Vo	Voltage output swing from rail		V _S = 5 V;	R _L ≥ 2 kΩ				1.5	
		Negative rail	V _S = 5 V;	R _L ≤ 10 kΩ	$T_A = -25^{\circ}\text{C to } 85^{\circ}\text{C}$		5	20	mV
						-20	-30		
		V _S = 15 V; V _O = 0 V; V _{ID} = 1 V	Source	LM258A				-60	
	Output aumant				T _A = -25°C to 85°C	-10			mA
lo	Output current	V _S = 15 V; V _O = 15 V; V _{ID} = -1	Sink			10	20		
		V	SILIK		T _A = -25°C to 85°C	5			
		$V_{ID} = -1 \text{ V}; V_{O} = 200 \text{ mV}$				12	30		μA
I _{sc}	Short-circuit current	$V_S = 10 \text{ V}; V_O = V_S / 2$					±40	±60	mA
POWER	SUPPLY	•			+			-	
I _Q	Quiescent current per amplifier	$V_0 = 2.5 \text{ V}; I_0 = 0 \text{ A}$			T _A = -25°C to 85°C		350	600	μA

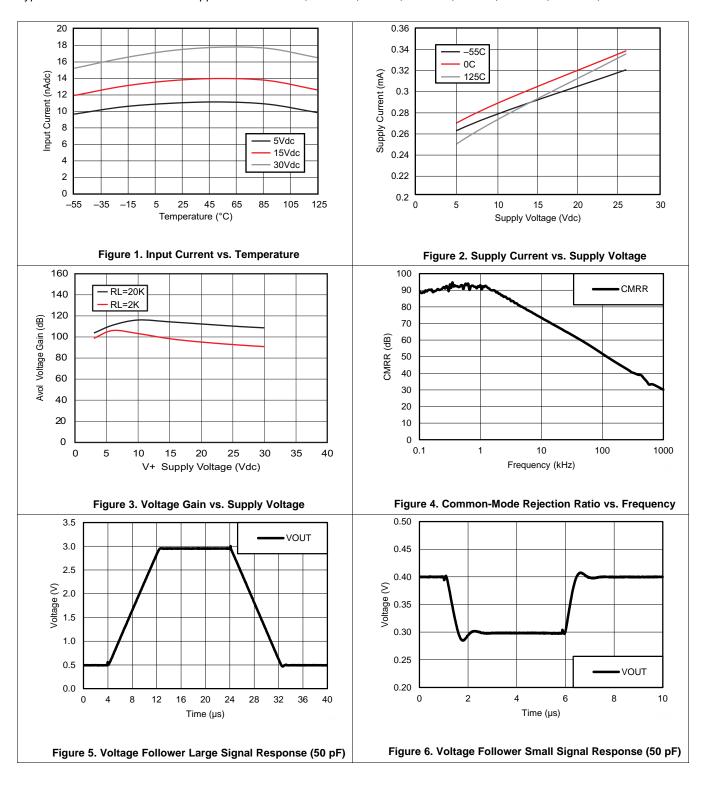
⁽¹⁾ All characteristics are measured under open-loop conditions, with zero common-mode input voltage, unless otherwise specified. Maximum V_S for testing purposes is 30 V for LM258 and LM258A.

All typical values are T_A = 25°C.



7.11 Typical Characteristics

Typical characteristics section is applicable for LM158, LM158A, LM258, LM258A, LM358A, LM358A, LM2904, and LM2904V





Typical Characteristics (continued)

Typical characteristics section is applicable for LM158, LM158A, LM258, LM258A, LM358A, LM358A, LM2904, and LM2904V

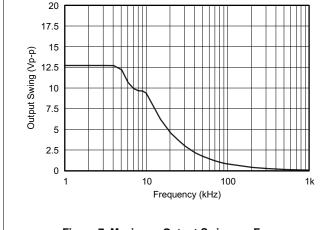


Figure 7. Maximum Output Swing vs. Frequency $(V_{CC} = 15 \text{ V})$

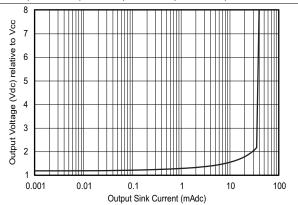
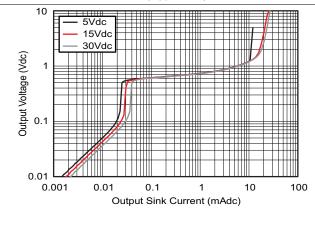


Figure 8. Output Sourcing Characteristics





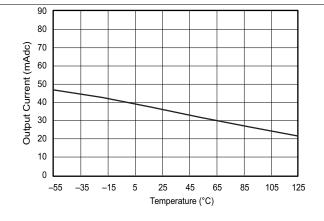


Figure 10. Source Current Limiting



8 Parameter Measurement Information

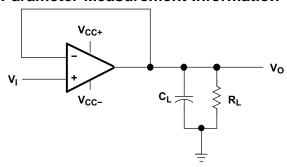


Figure 11. Unity-Gain Amplifier

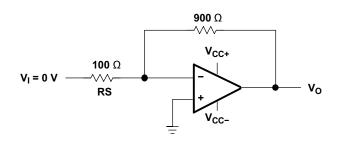


Figure 12. Noise-Test Circuit



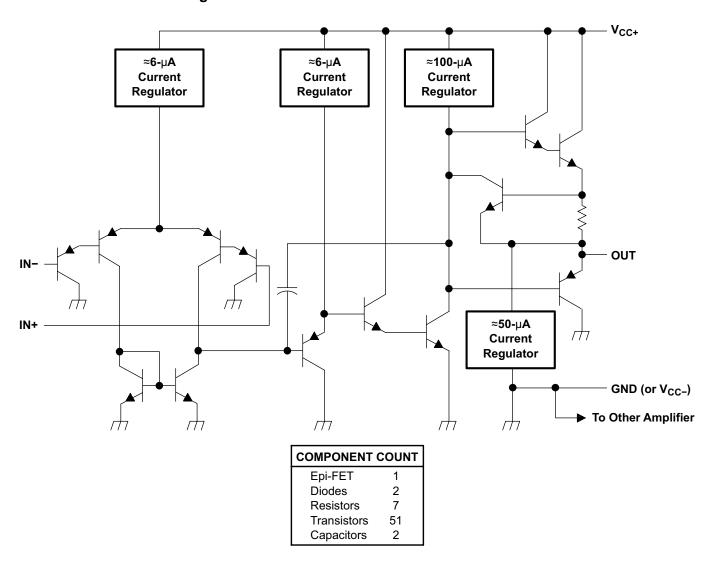
9 Detailed Description

9.1 Overview

These devices consist of two independent, high-gain frequency-compensated operational amplifiers designed to operate from a single supply over a wide range of voltages. Operation from split supplies also is possible if the difference between the two supplies is within the supply voltage range specified in the Recommended Operating Conditions section, and V_S is at least 1.5 V more positive than the input common-mode voltage. The low supply-current drain is independent of the magnitude of the supply voltage.

Applications include transducer amplifiers, dc amplification blocks, and all the conventional operational amplifier circuits that now can be implemented more easily in single-supply-voltage systems. For example, these devices can be operated directly from the standard 5-V supply used in digital systems and easily can provide the required interface electronics without additional ±5-V supplies.

9.2 Functional Block Diagram





9.3 Feature Description

9.3.1 Unity-Gain Bandwidth

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal. These devices have a 1.2-MHz unity-gain bandwidth (B Version).

9.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 0.5-V/µs slew rate (B Version).

9.3.3 Input Common Mode Range

The valid common mode range is from device ground to $V_S - 1.5 \text{ V}$ ($V_S - 2 \text{ V}$ across temperature). Inputs may exceed V_S up to the maximum V_S without device damage. At least one input must be in the valid input common-mode range for the output to be the correct phase. If both inputs exceed the valid range, then the output phase is undefined. If either input more than 0.3 V below V- then input current should be limited to 1 mA and the output phase is undefined.

9.4 Device Functional Modes

These devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier, depending on the application.

Submit Documentation Feedback



10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The LMx58 and LM2904 operational amplifiers are useful in a wide range of signal conditioning applications. Inputs can be powered before V_S for flexibility in multiple supply circuits.

10.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

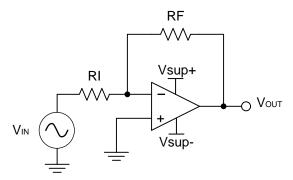


Figure 13. Application Schematic

10.2.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application scales a signal of ± 0.5 V to ± 1.8 V. Setting the supply at ± 12 V is sufficient to accommodate this application.

10.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using Equation 1 and Equation 2:

$$A_{V} = \frac{VOUT}{VIN}$$

$$A_{V} = \frac{1.8}{-0.5} = -3.6$$
(2)

Once the desired gain is determined, choose a value for R_I or R_F . [Subscripts should be fixed in the accompanying figures and equations also.] Choosing a value in the kilohm range is desirable because the amplifier circuit uses currents in the milliampere range. This ensures the part does not draw too much current. This example uses 10 k Ω for R_I which means 36 k Ω is used for R_F . This was determined by Equation 3.

$$A_{V} = -\frac{RF}{RI}$$
 (3)

Typical Application (continued)

10.2.3 Application Curve



Figure 14. Input and Output Voltages of the Inverting Amplifier

11 Power Supply Recommendations

CAUTION

Supply voltages larger than specified in the recommended operating region can permanently damage the device (see the *Absolute Maximum Ratings*).

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout* section.

12 Layout

12.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the
 operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low-impedance
 power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace. [Things in parallel never cross, by definition]
- Place the external components as close to the device as possible. Keeping R_F and R_G close to the inverting
 input minimizes parasitic capacitance, as shown in *Layout Examples*.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.



12.2 Layout Examples

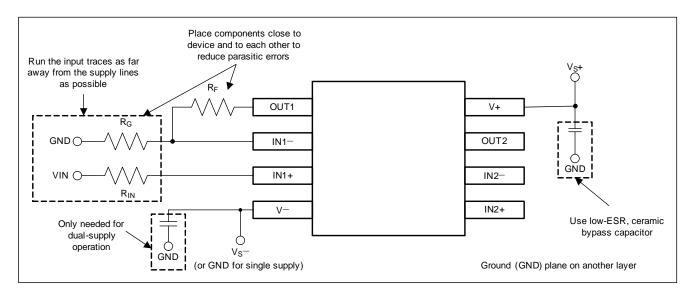


Figure 15. Operational Amplifier Board Layout for Noninverting Configuration

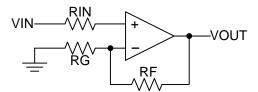


Figure 16. Operational Amplifier Schematic for Noninverting Configuration



13 Device and Documentation Support

13.1 Documentation Support

13.1.1 Related Documentation

Texas Instruments, Circuit Board Layout Techniques.

13.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

Table 1. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
LM158	Click here	Click here	Click here	Click here	Click here
LM158A	Click here	Click here	Click here	Click here	Click here
LM258	Click here	Click here	Click here	Click here	Click here
LM258A	Click here	Click here	Click here	Click here	Click here
LM358	Click here	Click here	Click here	Click here	Click here
LM358A	Click here	Click here	Click here	Click here	Click here
LM358B ⁽¹⁾	Click here	Click here	Click here	Click here	Click here
LM2904	Click here	Click here	Click here	Click here	Click here
LM2904B ⁽¹⁾	Click here	Click here	Click here	Click here	Click here
LM2904V	Click here	Click here	Click here	Click here	Click here

⁽¹⁾ Device is currently Preview

13.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

13.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.5 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

13.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.







13.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most-current data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser based versions of this data sheet, see the left-hand navigation pane.





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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Sample
5962-87710012A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 87710012A LM158FKB	Sample
5962-8771001PA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	8771001PA LM158	Sample
5962-87710022A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 87710022A LM158AFKB	Sample
5962-8771002PA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	8771002PA LM158A	Sample
LM158AFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 87710022A LM158AFKB	Sample
LM158AJG	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	LM158AJG	Sample
LM158AJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	8771002PA LM158A	Sample
LM158FKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 87710012A LM158FKB	Sample
LM158JG	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	LM158JG	Sample
LM158JGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	8771001PA LM158	Sample
LM258AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	LM258A	Sample
LM258ADGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-1-260C-UNLIM	-25 to 85	(M3L, M3P, M3S, M3 U)	Sample
LM258ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-25 to 85	LM258A	Sample
LM258ADRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	LM258A	Sample
LM258ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	LM258A	Sample
LM258AP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	N / A for Pkg Type	-25 to 85	LM258AP	Sample





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Orderable Device	Status	Package Type		Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LM258APE4	ACTIVE	PDIP	Р	8		Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-25 to 85	LM258AP	Samples
LM258D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	LM258	Samples
LM258DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	LM258	Samples
LM258DGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-1-260C-UNLIM	-25 to 85	(M2L, M2P, M2S, M2 U)	Samples
LM258DGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	(M2L, M2P, M2S, M2 U)	Samples
LM258DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-25 to 85	LM258	Samples
LM258DRG3	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-25 to 85	LM258	Samples
LM258DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-25 to 85	LM258	Samples
LM258P	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	N / A for Pkg Type	-25 to 85	LM258P	Samples
LM258PE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-25 to 85	LM258P	Samples
LM2904AVQDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904AV	Samples
LM2904AVQDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904AV	Samples
LM2904AVQPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904AV	Samples
LM2904AVQPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904AV	Samples
LM2904BIDR	PREVIEW	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 125		
LM2904D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples
LM2904DE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples
LM2904DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples





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Orderable Device	Status	Package Type	-	Pins	-		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LM2904DGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(MBL, MBP, MBS, MB U)	Samples
LM2904DGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(MBL, MBP, MBS, MB U)	Samples
LM2904DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples
LM2904DRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples
LM2904DRG3	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples
LM2904DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM2904	Samples
LM2904P	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	N / A for Pkg Type	-40 to 125	LM2904P	Samples
LM2904PE4	ACTIVE	PDIP	Р	8		Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 125	LM2904P	Samples
LM2904PSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904	Samples
LM2904PW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904	Samples
LM2904PWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	L2904	Samples
LM2904PWRG3	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	L2904	Samples
LM2904PWRG4-JF	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904	Samples
LM2904QDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904Q1	Samples
LM2904QDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	2904Q1	Samples
LM2904VQDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904V	Samples
LM2904VQDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904V	Samples
LM2904VQPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904V	Samples





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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LM2904VQPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	L2904V	Samples
LM358AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358A	Samples
LM358ADE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358A	Samples
LM358ADG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358A	Samples
LM358ADGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-1-260C-UNLIM	0 to 70	(M6L, M6P, M6S, M6 U)	Samples
LM358ADGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	(M6L, M6P, M6S, M6 U)	Samples
LM358ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	0 to 70	LM358A	Samples
LM358ADRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358A	Samples
LM358ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358A	Samples
LM358AP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	N / A for Pkg Type	0 to 70	LM358AP	Samples
LM358APE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	LM358AP	Samples
LM358APW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	L358A	Samples
LM358APWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	0 to 70	L358A	Samples
LM358APWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	L358A	Samples
LM358BIDR	PREVIEW	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 85		
LM358D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358	Samples
LM358DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358	Samples
LM358DGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-1-260C-UNLIM	0 to 70	(M5L, M5P, M5S, M5 U)	Samples





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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LM358DGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	(M5L, M5P, M5S, M5 U)	Samples
LM358DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	0 to 70	LM358	Samples
LM358DRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358	Sample
LM358DRG3	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM358	Sample
LM358DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LM358	Sample
LM358P	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	N / A for Pkg Type	0 to 70	LM358P	Sample
LM358PE3	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU SN	N / A for Pkg Type	0 to 70	LM358P	Sample
LM358PE4	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	0 to 70	LM358P	Sample
LM358PSR	ACTIVE	so	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	L358	Sample
LM358PW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	L358	Sample
LM358PWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	0 to 70	L358	Sample
LM358PWRG3	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	L358	Sample
LM358PWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	L358	Sample
LM358PWRG4-JF	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	L358	Sample
PLM2904BIDR	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 125		Sample
PLM358BIDR	ACTIVE	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 85		Sample

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

PACKAGE OPTION ADDENDUM



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OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LM258A, LM2904, LM2904B:

Automotive: LM2904-Q1, LM2904B-Q1

■ Enhanced Product: LM258A-EP, LM2904-EP

NOTE: Qualified Version Definitions:

- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity AO

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM258ADGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM258ADR	SOIC	D	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
LM258ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258ADRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258ADRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM258DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258DR	SOIC	D	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
LM258DRG3	SOIC	D	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
LM258DRG3	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258DRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM258DRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904AVQDR	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904AVQDRG4	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904AVQPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904AVQPWRG4	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1



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Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM2904DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM2904DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM2904DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904DR	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904DRG3	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904DRG3	SOIC	D	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
LM2904DRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904DRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904PWRG3	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904PWRG4-JF	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904QDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM2904VQDR	SOIC	D	8	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
LM2904VQPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM2904VQPWRG4	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358ADGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM358ADR	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358ADRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358ADRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358APWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358APWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358APWRG4	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM358DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM358DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358DR	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358DRG3	SOIC	D	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
LM358DRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358DRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM358PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358PWRG3	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358PWRG4	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LM358PWRG4-JF	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM258ADGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
LM258ADR	SOIC	D	8	2500	364.0	364.0	27.0
LM258ADR	SOIC	D	8	2500	340.5	338.1	20.6
LM258ADR	SOIC	D	8	2500	367.0	367.0	35.0
LM258ADRG4	SOIC	D	8	2500	340.5	338.1	20.6
LM258ADRG4	SOIC	D	8	2500	367.0	367.0	35.0
LM258DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
LM258DR	SOIC	D	8	2500	367.0	367.0	35.0
LM258DR	SOIC	D	8	2500	340.5	338.1	20.6
LM258DR	SOIC	D	8	2500	364.0	364.0	27.0
LM258DRG3	SOIC	D	8	2500	364.0	364.0	27.0
LM258DRG3	SOIC	D	8	2500	333.2	345.9	28.6
LM258DRG4	SOIC	D	8	2500	367.0	367.0	35.0
LM258DRG4	SOIC	D	8	2500	340.5	338.1	20.6
LM2904AVQDR	SOIC	D	8	2500	340.5	338.1	20.6
LM2904AVQDRG4	SOIC	D	8	2500	340.5	338.1	20.6
LM2904AVQPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904AVQPWRG4	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
LM2904DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0



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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM2904DR	SOIC	D	8	2500	340.5	338.1	20.6
LM2904DR	SOIC	D	8	2500	367.0	367.0	35.0
LM2904DR	SOIC	D	8	2500	333.2	345.9	28.6
LM2904DRG3	SOIC	D	8	2500	333.2	345.9	28.6
LM2904DRG3	SOIC	D	8	2500	364.0	364.0	27.0
LM2904DRG4	SOIC	D	8	2500	340.5	338.1	20.6
LM2904DRG4	SOIC	D	8	2500	367.0	367.0	35.0
LM2904PWR	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904PWR	TSSOP	PW	8	2000	364.0	364.0	27.0
LM2904PWRG3	TSSOP	PW	8	2000	364.0	364.0	27.0
LM2904PWRG4-JF	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904QDR	SOIC	D	8	2500	350.0	350.0	43.0
LM2904VQDR	SOIC	D	8	2500	340.5	338.1	20.6
LM2904VQPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
LM2904VQPWRG4	TSSOP	PW	8	2000	367.0	367.0	35.0
LM358ADGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
LM358ADR	SOIC	D	8	2500	333.2	345.9	28.6
LM358ADR	SOIC	D	8	2500	367.0	367.0	35.0
LM358ADR	SOIC	D	8	2500	340.5	338.1	20.6
LM358ADRG4	SOIC	D	8	2500	367.0	367.0	35.0
LM358ADRG4	SOIC	D	8	2500	340.5	338.1	20.6
LM358APWR	TSSOP	PW	8	2000	364.0	364.0	27.0
LM358APWR	TSSOP	PW	8	2000	367.0	367.0	35.0
LM358APWRG4	TSSOP	PW	8	2000	367.0	367.0	35.0
LM358DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
LM358DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
LM358DR	SOIC	D	8	2500	367.0	367.0	35.0
LM358DR	SOIC	D	8	2500	333.2	345.9	28.6
LM358DR	SOIC	D	8	2500	340.5	338.1	20.6
LM358DRG3	SOIC	D	8	2500	364.0	364.0	27.0
LM358DRG4	SOIC	D	8	2500	367.0	367.0	35.0
LM358DRG4	SOIC	D	8	2500	340.5	338.1	20.6
LM358PWR	TSSOP	PW	8	2000	367.0	367.0	35.0
LM358PWR	TSSOP	PW	8	2000	364.0	364.0	27.0
LM358PWRG3	TSSOP	PW	8	2000	364.0	364.0	27.0
LM358PWRG4	TSSOP	PW	8	2000	367.0	367.0	35.0
LM358PWRG4-JF	TSSOP	PW	8	2000	367.0	367.0	35.0

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004





SMALL OUTLINE INTEGRATED CIRCUIT



- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



PS (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



DGK (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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